

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION: Mitsuhiro YANO, et al.

SERIAL NO.: 09/891,925

GAU: 2811

FILED: June 27, 2001

EXAMINER: HU, S.

FOR: SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING SAME

LETTER SUBMITTING REPLACEMENT DRAWING SHEET(S)

COMMISSIONER FOR PATENTS

Alexandria, VA 22313

SIR:

Responsive to the below indicated communication, the following drawing sheets are submitted herewith:

2 Replacement Drawing Sheets _____ New Drawing Sheets

_____ Annotated Drawing Sheets

Official Action dated May 29, 2008

Notice of Allowance/Issue Fee dated _____

Other dated _____

The changes and/or modifications made include the following:

The original labeled element 16 under the gate layer 17 in Figure 2 is now newly labeled element 161, and is noted in the amended specification as formed of silicon oxide. Figure 8 is also herein amended to consistently refer to elements 8 and 7 and delete the original reference indicator "16".

Respectfully Submitted,

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